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List of Patents and Publications for Applicant's

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant

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Filing Date:

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Group:

2812

U.S. Patent Documents

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Foreign Patent Documents

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Other Art

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U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
TSP	A1	2002/0119250 A1	8/29/02	Campana <i>et al.</i>	427	255.28	
	A2	2003/0045098 A1	3/06/03	Verhaverbeke <i>et al.</i>	438	689	
TSP	A3	2003/0077916 A1	8/24/03	Xu <i>et al.</i>	438	778	
	A4						
	A5						

Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
TSP	B1	EP 1 061 156 A2	12/20/00	Europe	C23C	16/56	Yes
TSP	B2	EP 1 077 479 A1	2/21/01	Europe	H01L	21/316	Yes
	B3						

Other Art (Including Author, Title, Date Pertinent Pages, Etc.)

Exam. Init.	Ref. Des.	Citation
TSP	C1	Kim <i>et al.</i> , "Breakdown Phenomena in MIS Structure," <i>Proc. Of 3rd Int'l Conf. on Properties and Application of Dielectric Materials</i> , Tokyo, Japan, pp. 164-168, July 8-12, 1991.
TSP	C2	Shanware <i>et al.</i> , "Reliability evaluation of HiSiON gate dielectric film with 12.8 Å SiO ₂ equivalent thickness," <i>IEEE</i> , pp. 6.6.1-6.6.4, 2001.
TSP	C3	Abadeer <i>et al.</i> , "Key measurements of ultrathin gate dielectric reliability and in-line monitoring," <i>IBM J. Res. Develop.</i> , 43:407-16, 1999.

EXAMINER:

DATE CONSIDERED:

6/13/05

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